TOSHIBA TA7792PG/FG

TOSHIBA BIPOLAR LINEAR INTEGRATED CIRCUIT SILICON MONOLITHIC

# **TA7792PG, TA7792FG**

# AM/FM 1 CHIP TUNER SYSTEM IC (1.5V USE)

The TA7792PG, TA7792FG are AM/FM 1 chip tuner system (FM FRONT END + AM/FM IF) ICs, which are designed for low voltage operation (1.5V, 3.0V). Those are especially suitable for stereo headphone radio and radio cassette recorder equipments. These item can realize the low power dissipation and few external parts.

#### **FEATURES**

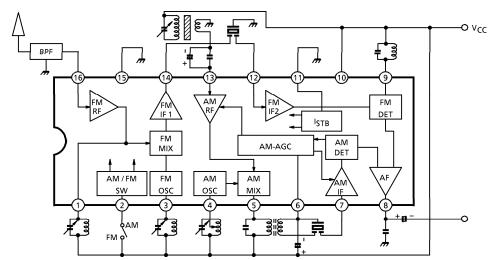
- AM detector coil-less
- FM mixer coil-less
- Switchover between AM/FM mode is possible with onemake switch.
- Operating supply voltage range
   VCC (opr) = 0.95~5V (Ta = 25°C)
- Excellent low supply current (V<sub>CC</sub> = 1.5V, Ta = 25°C)
   I<sub>CC</sub> (AM) = 1.2mA (Typ.)
   I<sub>CC</sub> (FM) = 4.0mA (Typ.)

# DIP16-P-300-2.54A TA7792FG SSOP16-P-225-1.00A

Weight DIP16-P-300-2.54A : SSOP16-P-225-1.00A : (

0-2.54A : 1.00g (Typ.) 25-1.00A : 0.14g (Typ.)

#### **BLOCK DIAGRAM**



TOSHIBA TA7792PG/FG

#### **APPLICATION NOTE**

#### <FM SECTION>

# • RF amplifier (See Fig.1)

This stage is composed of the emitter-grounded and cascade connection amplifier.

The input impedance of pin 6 is about 260  $\Omega$  , which is determined by D1.

# • Mixer amplifier (See Fig.2)

The amplified RF signal is transformed into IF signal by the mixer circuit which is composed of a differential amplifier.

The amplified IF signal is appeared through the emitter follower circuit at pin4. The output impedance of pin 4 is about 300 $\Omega$ , due to match the impedance of the ceramic filter.

#### (Note)

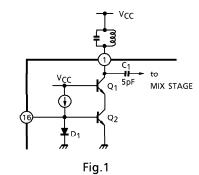
The spurious characteristic is determined by the characteristic of the ceramic filter (10.7MHz), because the mixer coil is dispensable. It is possible to improve the spurious characteristic that the two ceramic filters of different characteristics are connected in series.

# • IF limiter amplifier (See Fig.3)

The IF limiter amplifier is composed of six emittergrounded amplifiers and a differential amplifier. The basis composition of the emitter-grounded amplifiers is shown as Fig.3.

#### • Detector circuit

This stage is composed of the quadrature detector circuit, which has double balanced.



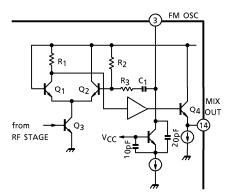


Fig.2

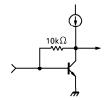


Fig.3

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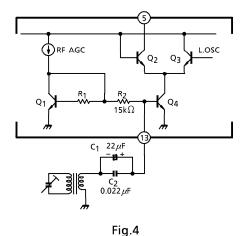
#### <AM SECTION>

#### • RF amplifier (See Fig.4)

This stage is composed of emitter-grounded amplifier, the input impedance of which has about 7.3k $\Omega$ . It is necessary to connect as Fig.4, because the condenser, C<sub>1</sub> is available to the audio by-pass of the RF-AGC, the noise of low frequency.

#### Mixer circuit

The amplified RF signal is transformed into IF signal by the mixer circuit, which is composed of a differential amplifier.



#### • IF amplifier

This stage is composed of four emitter-grounded amplifiers and the two differential amplifiers. The input impedance is rather high, because it is changed by the amplitude of input signal (AGC level). So the input terminal of the IF amplifier must be matched with the impedance of ceramic filter.

#### <COMMON SECTION>

#### AM / FM mode switchover

Switchover between AM/FM mode is possible with one-make switch. In case of the opened, this IC has AM mode.

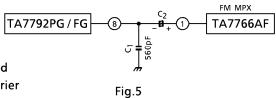
Another in case that the terminal is connected to  $V_{CC}$  directly, that has FM mode. And the terminal of pin@ is  $V_{CC}$  terminal of FM FRONT END section, too.

# • Output circuit (See Fig.5)

Both of the AM/FM detector signal is appeared through the pin®.

Those output are chosen by the mode switchover. At the same time, the output impedance is changed as follow at AM/FM mode, due to cut the AM carrier signal and pass the FM composite signal smoothly, with only one condenser.

 $R_{out}$  (AM) =  $8k\Omega$  (Typ.)  $R_{out}$  (FM) = 1.4 $k\Omega$  (Typ.)



# ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

CHARACTER	RISTIC	SYMBOL	RATING	UNIT	
Supply Voltage		Vcc	5	٧	
Power Dissipation	TA7792PG	P <sub>D</sub> (Note)	750	mW	
	TA7792FG	FD (Note)	350	IIIVV	
Operating Temper	ature	T <sub>opr</sub>	<b>- 25∼75</b>	°C	
Storage Temperati	ıre	T <sub>stg</sub>	<b>- 55∼150</b>	°C	

(Note) Derated above  $Ta = 25^{\circ}C$  in the proportion of  $6mW/^{\circ}C$  for TA7792PG, and of 2.8mW/°C for TA7792FG.

# **ELECTRICAL CHARACTERISTICS**

Unless otherwise specified, Ta = 25°C, V<sub>CC</sub> = 1.5V FM : V<sub>in</sub> = 60dB $\mu$ V EMF, f = 83MHz, f<sub>m</sub> = 1kHz,  $\Delta$ f =  $\pm$  22.5kHz AM : V<sub>in</sub> = 60dB $\mu$ V EMF, f = 1MHz, f<sub>m</sub> = 1kHz, MOD = 30%

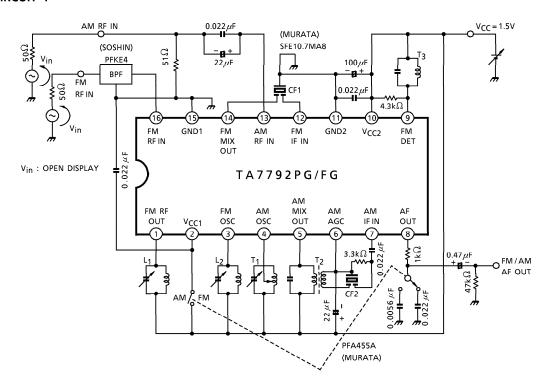
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CHARACTERISTIC		SYMBOL	TEST CIR- CUIT	CIR- TEST CONDITION		TYP.	MAX.	UNIT		
Cun	Supply Current		I <sub>CC</sub> (FM)	1	V <sub>in</sub> = 0	_	4.0	5.2	· mA	
Sup			I <sub>CC</sub> (AM)	1	V <sub>in</sub> = 0	_	1.2	1.8		
	Input Limiting Voltag	e	V <sub>in (lim)</sub>	1	- 3dB limiting	_	10	16	$dB\muV$ EMF	
	Total Harmonic Distor	rtion	THD (FM)	1		_	0.25	_	%	
	Signal To Noise Ratio		S / N (FM)	1		_	62	_	dB	
	Quiescent Sensitivity	Qs	1	S / N = 30dB	_	12	_	$dB\muV$ EMF		
FM	AM Rejection Ratio	AMR	1	MOD = 30%	_	30	_	dB		
	Oscillator Voltage	V <sub>osc</sub>	2	f = 60MHz	53	90	135	mVrms		
	Oscillator Stop Supply Voltage	V <sub>stop</sub> (FM)	1	$V_{in}$ < – 20dB $\mu$ V EMF	_	0.85	0.95	V		
	Recovered Output Vo	V <sub>OD</sub> (FM)	1		28	45	68	mVrms		
	Voltage Gain		GV	1	$V_{in} = 30 dB \mu V EMF$	14	25	50	mVrms	
	Recovered Output Voltage		V <sub>OD</sub> (AM)	1		25	40	60	mVrms	
١	Total Harmonic Distortion		THD (AM)	1		_	1.5	_	%	
AM	Signal To Noise Ratio	S/N(AM)	1		_	40	_	dB		
	Oscillator Stop Supply Voltage	V <sub>stop</sub> (AM)	1	$V_{in}$ < - 20dB $\mu$ V EMF	_	0.85	0.95	V		
	Output Resistance Pin® FM AM		R <sub>o</sub> (FM)	1	f = 1kHz	_	1.4		kΩ	
			R <sub>o</sub> (AM)	1	f = 1kHz	_	8	_	K77	

※ V<sub>in</sub>: Open Display

**TERMINAL VOLTAGE** : Terminal voltage at no signal with test circuit ( $V_{CC} = 1.5V$ ,  $Ta = 25^{\circ}C$ )

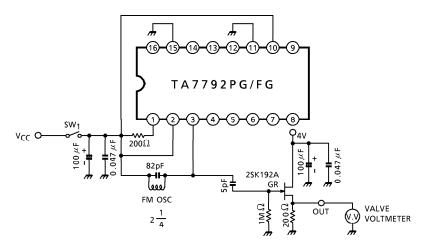
PIN No.		SYMBOL	TYP.		UNIT		PIN No.	SYMBOL	TYP.		UNIT	
	PIN NAME	STIVIBOL	AM	FM	OIVII	'' PIN NAME		STIVIBOL	AM	FM	CIVII	
1	FM RF OUT	V <sub>1</sub>	_	1.5	V	9	FM DET	V9	1.5	1.5	V	
2	V <sub>CC1</sub>	V <sub>2</sub>	_	1.5	V	10	V <sub>CC2</sub>	V <sub>10</sub>	1.5	1.5	V	
3	FM OSC	V <sub>3</sub>	_	1.5	V	11	GND2	V <sub>11</sub>	0	0	V	
4	AM OSC	V <sub>4</sub>	1.5	1.5	V	12	FM IF IN	V <sub>12</sub>	_	0.7	V	
5	AM MIX OUT	V <sub>5</sub>	1.5	1.5	V	13	AM RF IN	V <sub>13</sub>	0.7	_	V	
6	AM AGC	٧6	0.8	_	V	14	FM MIX OUT	V <sub>14</sub>	_	0.8	V	
7	AM IF IN	V <sub>7</sub>	1.4	1.5	V	15	GND1	V <sub>15</sub>	0	0	V	
8	AF OUT	V <sub>8</sub>	0.6	0.6	V	16	FM RF IN	V <sub>16</sub>	-	0.7	V	

# **TEST CIRCUIT 1**



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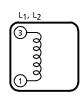
# **TEST CIRCUIT 2**

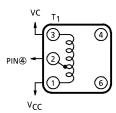


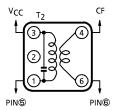
# **COIL DATA** (Test circuit)

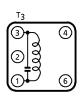
S: SUMIDA ELECTRIC Co., Ltd.

COIL STAGE	TEST	L (μΗ)	C <sub>0</sub> (pF)	Q <sub>0</sub>		TU	RN		WIRE	REFERENCE	
COIL STAGE	FREQUENCY				1-2	2-3	1-3	4-6	$(mm\phi)$		
L <sub>1</sub> FM RF	100MHz	0.053	l	100	_		$1\frac{3}{4}$		0.5UEW	© 0258-000-020	
L <sub>2</sub> FM OSC	100MHz	0.065	1	100	_	_	$2\frac{1}{4}$	_	0.5UEW	© 0258-000-021	
T <sub>1</sub> AM OSC	796kHz	288	l	115	13	73		-	0.08UEW	<b>\$ 4147-1356-038</b>	
T <sub>2</sub> AM IFT	455kHz	_	180	120	_	_	180	15	0.06UEW	<b>\$</b> 2150-2162-165	
T <sub>3</sub> FM DET	10.7MHz	_	82	110		_	13	_	0.12UEW	<b>\$ 4152-4095-015</b>	

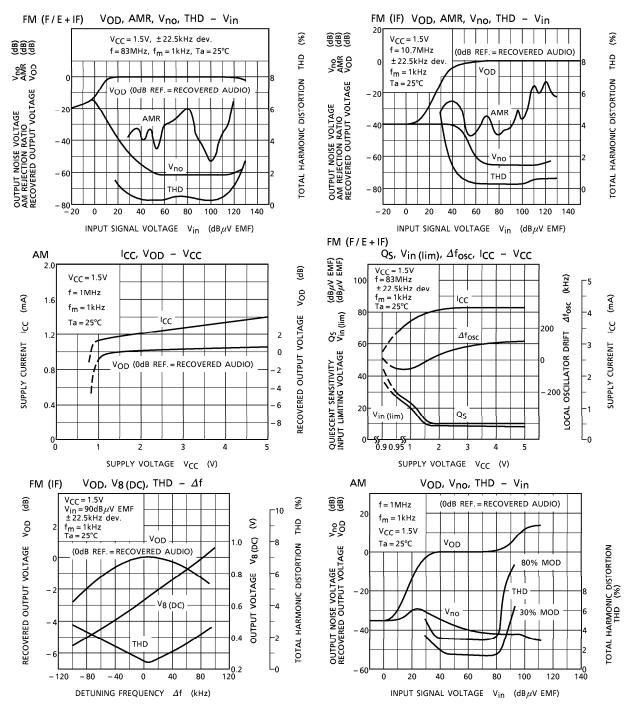








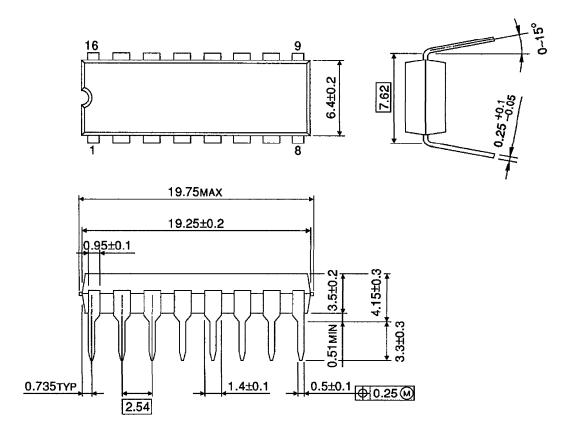
#### **CHARACTERISTICS CURVES**



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# PACKAGE DIMENSIONS DIP16-P-300-2.54A

Unit: mm

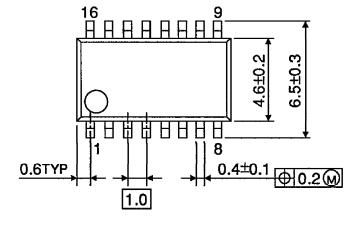


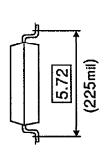
Weight: 1.00g (Typ.)

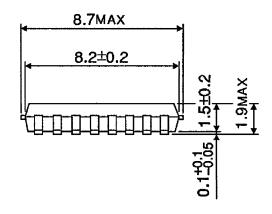
Unit: mm

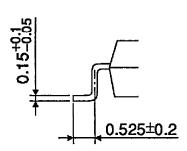
# PACKAGE DIMENSIONS

SSOP16-P-225-1.00A









Weight: 0.14g (Typ.)

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About solderability, following conditions were confirmed

- Solderability
  - (1) Use of Sn-37Pb solder Bath
    - · solder bath temperature = 230°C
    - · dipping time = 5 seconds
    - · the number of times = once
    - · use of R-type flux
  - (2) Use of Sn-3.0Ag-0.5Cu solder Bath
    - solder bath temperature = 245°C
    - · dipping time = 5 seconds
    - · the number of times = once
    - · use of R-type flux